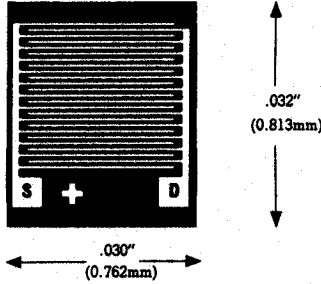


CHIP NUMBER
FN9.1



Die Size: 30 x 32 (mils)
0.762 x .813(mm)
Pad Size: .762 x .813(mils)
0.102 x 0.102(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

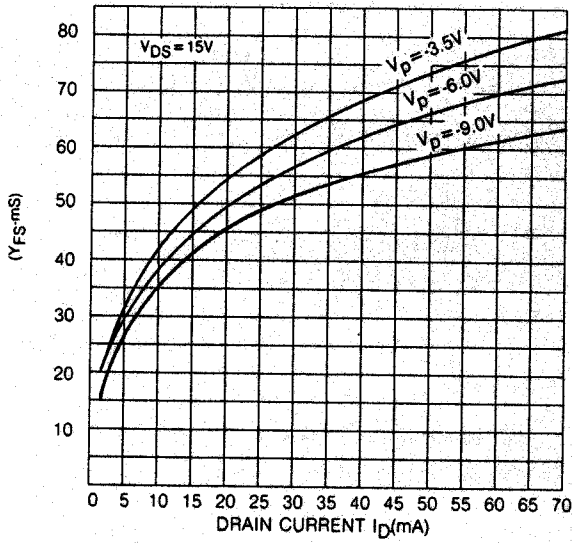
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	- 25	- 40	- 50	V	V _{DS} = 0, I _G = 1μA
I _{DSS}	30		1000	mA	V _{DS} = 15V, V _{GS} = 0
V _p	-1.0		-10	V	V _{DS} = 5V, I _D = 1nA
R _{on}	3.5		15	OHms	V _{GS} = 0, I _D = 10mA
I _{GSS}		30	200	pA	V _{DS} = 0, V _{GS} = -15V
C _{iss}		28	50	pF	V _{DS} = 0, V _{GS} = -10V, f = 1MHz
C _{rss}		14	25	pF	V _{DS} = 0, V _{GD} = 10V, f = 1MHz
g _{fs}	75	120	250	ms	V _{DS} = 15V, V _{GS} = 0, f = 1KHz

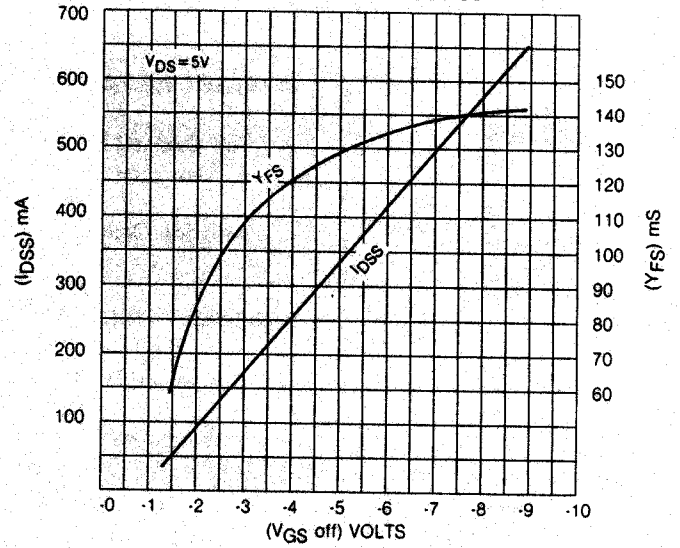
TYPICAL DEVICE TYPES: 2N5432 - 2N5434, series

CHIP TYPE FN9.1

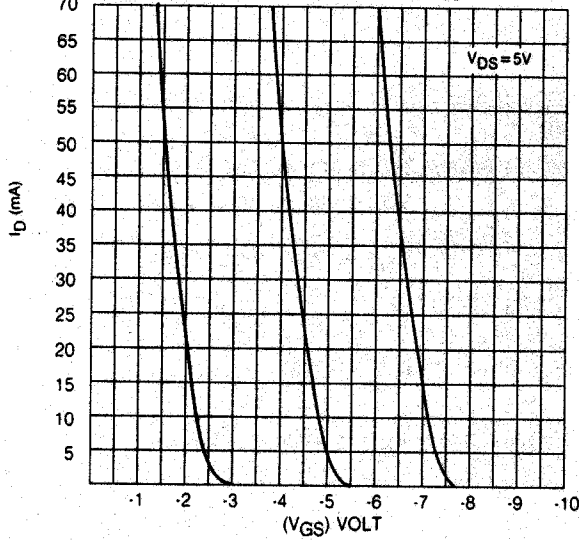
**FORWARD TRANSADMITTANCE
VS. OPERATING DRAIN CURRENT**



**FORWARD TRANSADMITTANCE VS
GATE-SOURCE CUTOFF VOLTAGE**



TRANSFER CHARACTERISTICS



OUTPUT CHARACTERISTICS

